Spectroscopy and Reactions of Hydrazoic Acid on Silicon Single Crystal Surfaces. (II). HN₃ and DN₃ on Si (100)

by

Jason C. S. Chu, Yue Bu and M. C. Lin
Department of Chemistry
Emory University
Atlanta, GA 30322

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Spectroscopy and Reactions of Hydrazoic Acid on Silicon Single Crystal Surfaces. (II). HN$_3$ and DN$_3$ on Si (100)

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ABSTRACT

Hydrazoic acid (HN$_3$) was employed for the first time as a nitrogen source for nitridation of Si surfaces. Its spectroscopy and reactions on different low Miller index surfaces have been investigated with XPS, UPS (X-ray and ultra-violet photoelectron spectroscopy), AES (Auger electron spectroscopy) and HREELS (high resolution electron energy loss spectroscopy) at temperatures between 120 and 1350 K. This study focuses on the spectroscopy and reactions on the Si(100) surface. HN$_3$ was found to adsorb molecularly on these surfaces since all molecular vibrational peaks such as the HN-NN stretching vibration at 150 meV, the HNN=N stretching vibration at 270 meV and the H-N$_3$ stretching vibration at 415 meV could be clearly observed by HREELS. These assignments were confirmed by an isotopic study using DN$_3$.

Warming the surface from 120 to 250 K caused HN$_3$ to desorb as well as to decompose into N$_2$ and NH, which further dissociated to produce N and H as the surface was annealed from 580 to 800 K. The presence of H adatoms was revealed by the appearance of the Si-H stretching vibration at 267 meV. At $T_s > 800$ K, H atoms began to desorb, while N remained on the surface forming Si$_3$N$_4$ at $T_s \approx 1350$ K. These observations were fully corroborated by UPS, XPS and AES data. The results of AES and UPS analyses also indicate that nitrogen could diffuse into the bulk of Si (100), similar to the Si(110) case.

KEYWORDS: Silicon (100); Hydrazoic acid; Nitridation; Characterization.

1. INTRODUCTION

Silicon nitride (Si$_3$N$_4$) has been employed in a variety of semiconductor processing procedures and devices, such as oxidation mask, diffusion barriers and annealing caps, among others (1). The most commonly used compound for silicon nitridation is ammonia, which is very stable and usually requires high temperature or enhancement with electrical discharge or lasers (1,2).
In this series of studies, we have explored the applicability of hydrazoic acid which, unlike hydrazine, can be prepared with high purity and is chemically more labile than NH$_3$ and N$_2$H$_4$. The dissociation energy of the HN-N$_2$ bond is about 380 kJ/mole weaker than that of the H-NH$_2$ bond (3). This allows us to lower the processing temperature and also eliminate the need for external activations with lasers or electrical discharges.

In our preliminary study of the thermal stability of HN$_3$ on Si(110) between 120 and 1350 K, characterized by UPS and HREELS, we have found that HN$_3$ started to dissociate into NH and N$_2$ at temperatures as low as 220 K (4). The NH species dissociated further to produce N and H as the surface was annealed from 580 to 800 K. The H adatom, which appeared distinctively with the Si-H stretching vibration at 256 meV, began to desorb at $T_s > 800$ K, with the remaining Si$_x$N species transformed into Si$_3$N$_4$ at $T_s = 1350$ K. This decomposition mechanism was fully corroborated by the results of UPS and HREELS analyses (4).

In the present work, we have carried out a detailed study on the spectroscopy and decomposition mechanism of HN$_3$ and DN$_3$ on Si(100) using UPS, XPS and HREELS. The result of this study is presented herein and compared in some detail with the Si (110) data (4).

2. EXPERIMENTAL

The experiment was carried out in an ultra-high vacuum (UHV) system with multiple surface diagnostics, which include XPS, AES, UPS, HREELS and LEED (low energy electron diffraction) (4). The UHV system, which has a base pressure of about $5 \times 10^{-9}$ Pa, consists of four different compartments: preparation/deposition, XPS/UPS/AES, LEED and HREELS. Surface samples can be directly transferred from the prep-chamber to other analysis compartments via interlocks under UHV conditions.

The HREELS spectroscopic measurement was performed with an electron beam having the primary energy of $E_p = 5$ eV. The resolution was $\Delta E$ (FWHM) = 7 meV in the straight through mode. Angular dependence could be studied by rotating the movable energy analyzer around the axis perpendicular to the incident plane of the e-beam.

The UPS and XPS measurements were carried out with He II at 40.8 eV and Al K$_{\alpha 1,\alpha 2}$ at 1486.6 eV, respectively. Both analyses were made with a 180° hemispherical electrostatic condenser analyzer for electron detection.

Si(100) samples, obtained from Virginia Semiconductor Co. as highly polished discs, were cut into $1.5 \times 1.0$ cm$^2$ chips. These chips were cleaned with dilute hydrofluoric acid solution and then rinsed with de-ionized water. The mounted Si(100) sample was further cleaned by repeated annealing at $T_s > 1470$ K until no detectable C, N and O by XPS, AES and HREELS.
HN₃ and DN₃ were prepared by acidification of NaN₃ (Aldrich) with 60% H₃PO₄ and D₃PO₄, respectively. Both forms of phosphoric acid were also purchased from Aldrich with purities greater than 99%. The generated hydrazoic acid was purified through a chain of cold traps maintained at 195 K (dry ice), 160 K (ethanol slush) and 77 K (liquid N₂) under constant diffusion-pumping. FTIR analysis of the purified sample showed no detectable impurities. From this analysis, the DN₃ sample was found to have about 95% D-enrichment.

3. RESULTS and DISCUSSION

3.1 HREELS

Figure 1 shows a series of HREELS spectra taken from a 2.5 ± 0.5 L (Langmuir) HN₃ dosed Si(100) sample at 120 K and annealed at the indicated temperatures. When dosed at 120 K, peaks at 56, 153 (shoulder), 163, 272 and a broad weak peak at ~415 meV were observed. By analogy to earlier IR/Raman studies (5,6), these peaks can be assigned to the different modes of molecular vibrations as shown in Table 1. The good agreement between the IR/Raman and our HREELS spectra suggests that HN₃ molecules were essentially associatively adsorbed on the surface. However, the peak at 56 meV and the broad peak at ~415 meV may imply the formation of the dimers to some extent upon adsorption because of the relatively high dosage employed in the present work. The 56 meV peak may have contribution from the H-bond torsion vibration in dimer at 48 meV besides the two N₃ bending vibrations and the 415 meV peak may have contributions from N-H stretching vibrations at 394 and 411 meV, as observed in HN₃ dimers (6).

When the sample was annealed at 520 K, the following changes were observed. Firstly, all peak intensities were attenuated by more than two times, which obviously suggests the partial desorption of the adsorbed species. In addition, the peak at 58 meV shifted to 77 meV and the peak at 415 meV shifted to 428 meV with its FWHM being significantly reduced. These changes are probably mainly due to the breaking of the dimers. Furthermore, since a peak at 422 meV was observed for NHₓ species adsorbed on Si substrates (7,8), the peak at 428 meV observed here, together with the appearance of a new peak at 110 meV due to Si-NHₓ stretching vibration, also suggests some cracking of the HN-NN bond and thus forming the adsorbed NHₓ species. This HN-NN bond cleavage was essentially complete when the surface was annealed at 610 K. At this temperature, all HN₃ molecular vibration peaks were absent, the spectrum was dominated by a broad peak at 110 meV due to different bonding between Si and NHₓ (9-12). Meanwhile the new peak at 267 meV due to the Si-H stretching vibration indicates the dissociation of some N-H species. The latter was further confirmed by the spectrum recorded after annealing the sample at 800 K, where 267 meV peak grew bigger and the N-H stretching vibration at 428 meV essentially disappeared.

Further annealing the sample to higher temperatures caused Si-N bonding structure change as evidenced by the shifting of the Si-N peak position and the variation in peak intensities.
FIGURE 1. HREEL spectra of 2.5 ± 0.5 L HN₃ dosed Si(100) recorded at 120 K after annealing at the indicated temperatures.
Similar peak shifting and intensity variation were also observed in the earlier IR (13) and HREELS (14, 15) studies of NH$_3$ on Si substrates.

A similar experiment was also carried out with DN$_3$ to confirm some of the HREELS peak assignments. As shown in Figure 2, upon dosing 2.5 ± 0.5 L DN$_3$ on Si (100) at 120 K, peaks at 60, 128, 153, 271 and a shoulder at ~300 meV were evident. The spectrum clearly shows the isotopic effect on the corresponding molecular vibration frequencies. Comparison of the peak assignments with those of IR/Raman spectra is also given in Table 1.

It should be pointed out that because of the fast hydrogen-deuterium exchange on the walls of the chamber and inlet line, the corresponding HN$_3$ peaks also appeared in the DN$_3$ HREELS spectra. When the sample was annealed at various temperatures, essentially the same results as HN$_3$ on Si(100) were found, although the spectra were more complicated due to the existence of both HN$_3$ and DN$_3$ species on the surface. An additional spectrum after annealing at 250 K is also shown in Figure 2, which is nearly identical to that of the 520 K spectrum. Thus the annealing effect discussed above for HN$_3$ on Si(100) at 520 K should also apply to the spectrum at 250 K, if it were recorded. In fact, a similar annealing effect was found for HN$_3$ on Si(110) at as low as 220 K (4).

3.2. UPS

Figure 3 shows the temperature dependence of UPS spectra of 2.0 ± 0.5 L HN$_3$ dosed Si(100). When dosed at 120 K, UPS (He II) spectra exhibited peaks at 4.7, 6.7, 8.9 eV below EF. In addition, a shoulder at 10.3 eV with a long tail extended to the higher binding energy (B.E.) side was also visible. By comparing with the gaseous HN$_3$ UPS results (16), Table 1. Vibrational frequencies (in meV) and assignments for HN$_3$ and DN$_3$ in the gas phase and on Si surfaces.

<table>
<thead>
<tr>
<th>Vibrational Mode</th>
<th>Gas$^a$</th>
<th>Si(100)$^b$</th>
<th>Si(110)$^c$</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td>HN$_3$</td>
<td>DN$_3$</td>
<td>HN$_3$DN$_3$</td>
</tr>
<tr>
<td>δ (N$_3$)</td>
<td>66</td>
<td>61</td>
<td>56</td>
</tr>
<tr>
<td>δ (N$_3$)</td>
<td>75</td>
<td>73</td>
<td>—</td>
</tr>
<tr>
<td>υ (HN-N$_2$); (DN-N$_2$)</td>
<td>143</td>
<td>147</td>
<td>153</td>
</tr>
<tr>
<td>β (H-N); (D-N)</td>
<td>157</td>
<td>118</td>
<td>163</td>
</tr>
<tr>
<td>υ (HN$_2$=N); (DN$_2$=N)</td>
<td>265</td>
<td>262</td>
<td>272</td>
</tr>
<tr>
<td>υ (N-H); (N-D)</td>
<td>414</td>
<td>307</td>
<td>415</td>
</tr>
</tbody>
</table>

a. Refs. (5) and (6). b. This work. c. Ref. (4)
FIGURE 2. HREEL spectra of 2.5 ± 0.5 L DN₃ dosed Si(100) recorded at 120 K after annealing at the indicated temperatures.
these peaks can be assigned to the $2a''$, $9a'$, and $8a'$ molecular orbitals and the shoulder at $-10.3$ eV to the $7a'$ orbital. The tail in the spectra should be due to the $1a''$ and $6a'$ molecular orbitals, respectively.

When the surface was annealed at 520 K, the peaks at 4.7 and 8.9 eV were attenuated. On the other hand, the peak at 6.7 eV was enhanced and shifted to $-6.9$ eV. Additionally, a new peak at 12.1 eV appeared. The peak intensity attenuation at 4.7 and 8.9 eV reflects the partial desorption of the adsorbed species, while the 6.7 and 12.1 eV peak enhancement suggests the formation of the Si-N bond due to the dissociation of HN$_3$ molecules, since Si-NH$_x$ species were found to show peaks at the similar energy positions. The energy separation of 5.2 eV between the two peaks observed here agrees very well with those of UPS results for a SiN$_x$:H (x=1) film (17) and an NH$_3$ dosed Si(111) sample (18). In the latter case, NH$_3$ molecules were believed to be dissociatively adsorbed on the surface and the energy separation between the two UPS peaks ranged from 5.25 to 5.7 under different experimental conditions.

Further annealing the sample from 620 to 950 K caused a shrinking of the 12.1 eV peak due to the N-H bond (19) and a further enhancement of the peak at $-7$ eV. These changes can be attributed to the cracking of the N-H bond and further formation of the Si-N bond, in consistence with our HREELS observation in the same temperature range. The UPS spectrum recorded after annealing the sample at 1180 K was similar to that of the clean surface (dashed line) except the three noticeable humps at 4.5, 7 and 11.5 eV, respectively. On the other hand, HREELS and XPS results did not show any obvious N-signal attenuation by annealing the sample at the same temperature. Therefore the annealing effect observed in the 1180 K UPS spectrum as well as the AES result, which also showed an N-signal intensity decrease at high annealing temperatures, suggests the occurrence of N-atom diffusion into the subsurface so that they cannot be detected effectively by the UPS and AES techniques. Similar observations were made in the case of HN$_3$ on Si(110) (4) and were also reported by Taguchi et al. (14) and Avouris et al. (20) in the nitridation of Si(100) surfaces. However, in an on-going study of HN$_3$ on Si(111), a very strong UPS peak at 7.5 eV, due to SiN species, persisted after the sample was annealed at similar temperatures (21). Finally, it should be pointed out that the three humps at 4.5, 7 and 11.5 eV compare favorably with UPS results taken from Si$_3$N$_4$ samples (19,22).

### 3.3 XPS

Figure 4 shows a series of XPS spectra taken by dosing $2.0\pm0.5$ L HN$_3$ on Si(100) at 120 K and then annealing the sample at the indicated temperatures. At 120 K, peaks at 404.7 and 400.8 eV with FWHM's of 3.8 and 2.5 eV, respectively, were observed; these peaks correlate well with the XPS results taken from solid HN$_3$ samples by Lee et al. (16). The peak at 404.7 eV is due to the central N atom, while the peak at 400.8 eV with a larger
FIGURE 3. UPS spectra of 2 ± 0.5 L HN₃ closed Si(100) recorded at 120 K after annealing at the indicated temperatures.

FIGURE 4. XPS spectra of 2 ± 0.5 L HN₃ dosed Si(100) recorded at 120 K after annealing at the indicated temperatures.
FWHM is due to the two terminal N atoms. These two terminal N atoms have different atomic charges (16, 23) in HN₃ molecules, thus the peak can be deconvoluted into two peaks (with equal intensity and FWHM) at 400.2 and 401.2 eV, as shown in Figure 4 by the dashed curve.

As the sample was annealed at 520 K, all peaks were significantly attenuated, broadened and shifted toward the lower B.E. side. The peak intensity decrease is obviously due to the desorption of the adsorbate, while the peak broadening and shifting may be due to the following possibilities. Firstly, the partial dissociation of the HN-NN bond as well as the breaking of the dimers possibly existed at 120 K as discussed in the HREELS section. The broad peak centered at 399.8 eV should have contributions from NH species, which was expected to show a peak at 399 eV (18), and the breaking down of dimers, i.e. the disappearance hydrogen bonding also tends to shift the N peaks towards lower B. E.'s (24). Secondly, charging-effect change due to desorption and dissociation of the adsorbate could also cause the N XPS peaks shift. Thirdly, the possibility of N₃ species formation, due to the breaking of the H-N₃ bond, may be induced by X-ray irradiation. The X-ray induced H species desorption and N-H stretching vibration peak intensity attenuation, because of the breaking of the H-N bond, was noted in both NH₃ (25) and N₂H₄ (8) adsorbed on Si(111). To the best of our knowledge, there is no N₃ XPS information available at the present time; however, the XPS spectrum of N₃⁻ negative ions does show a shift towards the lower B.E. side for both N peaks as compared to those of HN₃ XPS (16).

At 610 K and above, only one major peak at 397.5 eV was evident, which, according to previous studies (19, 26, 27), is due to atomic N on Si substrates; this indicates the formation of Si-nitride following the dissociation of the N-H bond. The tail at the higher B.E. side of the 397.5 eV peak in the 610 K spectrum is due to the incompletely dissociated NH species. Finally, at 1300 K the peak shifted back to 397.7 eV, indicating the change in the Si-N bonding structure and the diffusion of N atoms into the subsurface to form Si-nitride insulating layers (19).

4. CONCLUSIONS

When 2.5 L HN₃ was dosed on a Si(100) surface at 120 K, the molecules were found to be molecularly adsorbed on the surface with possible formation of dimers to some extent. HREELS study of DN₃ was also carried out to confirm some of the EELS peak assignments. Upon annealing the sample at 250 K, HN₃ started to dissociate into N₂ and NH species accompanied by partial desorption. The HN-NN bond breaking was essentially complete at Tₛ > 620 K. Further annealing the surface caused the breaking of the N-H bond, the desorption of H species and the formation of Si-nitride. At Tₛ > 1000 K, the significant attenuation of N signals in UPS and AES spectra, but not in HREELS and XPS spectra, suggests that N atoms can readily diffuse into the Si(100) substrate. These results were essentially the same as those observed in our recent study of HN₃ (DN₃) on Si (110).
5. ACKNOWLEDGMENT

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6. REFERENCES


7. BIOGRAPHIES

Jason C.S. Chu is a Ph.D candidate in the Department of Chemistry, Emory University, studying under the direction of M. C. Lin.

Yue Bu is a Senior Research Associate in the Department of Chemistry, Emory University, working under the supervision of M. C. Lin. He came to Emory after receiving his Ph.D degree at Brown University, Providence, RI in 1990. His thesis work was focused on the studies of the efficiency of ionization of alkali atoms on Si and Pt surfaces as it varied with the surface temperature and the kinetic energy of the atoms reaching the surface. He worked as a teaching assistant for three years after receiving his B.S. at Xiamen University, P.R. China.

M.C. Lin is Robert W. Woodruff Professor of Physical Chemistry at Emory University. He joined the University in 1988 after working for more than 19 years at the U.S. Naval Research Laboratory in Washington D.C., where he was Senior Scientist for Chemical Kinetics. He completed his Ph.D. degree in 1965 at the University of Ottawa, Canada and spent two years at Cornell University as a postdoctoral research associate before joining NRL. He has authored/coauthored more than 200 technical papers in the various areas of physical chemistry—chemical kinetics, chemical lasers and the applications of lasers to studies of combustion, propulsion and heterogeneous chemical processes (including etching, CVD and OMCVD). He has been awarded the Hillebrand Prize (Chemical Society of Washington, 1975), Physical Sciences Award (The Washington Academy of Sciences, 1976), Purce Science Award (Sigma Xi, 1979), Navy Meritorious Civilian Service Award (1979), Guggenheim Fellowship (1982) and Alexander von Humboldt Award (1982).